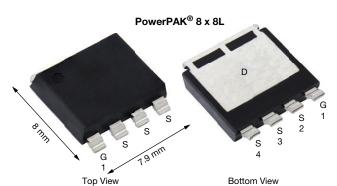
RoHS

COMPLIANT

HALOGEN FREE



N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	80
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.00135
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.00158
Q _g typ. (nC)	103
I _D (A) ^a	302
Configuration	Single

FEATURES

- TrenchFET® Gen V power MOSFET
- Fully lead (Pb)-free device
- Very low R_{DS} x Q_g figure of merit (FOM)
- Up to 302 A maximum continuous drain current
- 50 % smaller footprint than D2PAK (TO-263)
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

- · Synchronous rectification
- OR-ing
- Motor drive control
- · Battery management

G	
N-Channel MOSFET	os

ORDERING INFORMATION		
Package	PowerPAK 8 x 8L	
Lead (Pb)-free and halogen-free	SIJH5800E-T1-GE3	

ABSOLUTE MAXIMUM RATING	iS (T _A = 25 °C, u	ınless otherv	wise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V_{GS}	±20	V
	T _C = 25 °C		302	
0 " 1 7 17 17 17 17 17 17 17 17 17 17 17 17	T _C = 70 °C	1 .	253	
Continuous drain current (T _J = 175 °C)	T _A = 25 °C	I _D	30 p	
	T _A = 70 °C	†	25 ^b	Α
Pulsed drain current (t = 100 μs)		I _{DM}	500	^
Continuous source-drain diode current	T _C = 25 °C	lc	303	
	T _A = 25 °C		3 b	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	75	
Single pulse avalanche energy		E _{AS}	281	mJ
Maximum power dissipation	T _C = 25 °C		333	
	T _C = 70 °C	P _D	233	w
	T _A = 25 °C		3.3 b	VV
	T _A =70 °C	1	2.3 ^b	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c			260	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient ^b	Steady state	R _{thJA}	36	45	°C/W	
Maximum junction-to-case (drain)	Steady state	R _{thJC}	0.36	0.45	0/ ٧٧	

Notes

a. $T_C = 25$ °C

b. Surface mounted on 1" x 1" FR4 board
c. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



www.vishay.com

Vishay Siliconix

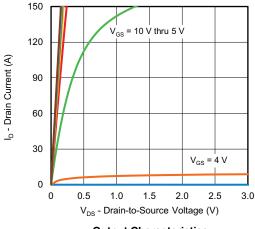
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V_{DS}	V _{GS} = 0 V, I _D = 1 mA	80	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	36	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-9.7	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	-	4	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20$	-	-	100	nA	
Zero gate voltage drain current		V _{DS} = 64 V, V _{GS} =0 V	-	-	1	μА	
	I _{DSS}	V _{DS} = 64 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15		
Duning and the second of the s	_	V _{GS} = 10 V, I _D = 20 A	-	0.00097	0.00135	0	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 7.5 V, I _D = 20 A	-	0.0012	0.00158	Ω	
Forward transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 75 A	-	170	-	S	
Dynamic ^b							
Input capacitance	C _{iss}		-	7730	-		
Output capacitance	C _{oss}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	2442	-	pF	
Reverse transfer capacitance	C _{rss}		-	20	-		
Total sets shows	0	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	103	155		
Total gate charge	Q _g		-	78	120		
Gate-source charge	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	_	35	-	nC	
Gate-drain charge	Q _{gd}		-	11	-		
Gate resistance	R_g	f = 1 MHz	0.34	1.7	3.4	Ω	
Turn-on delay time	t _{d(on)}		-	20	40		
Rise time	t _r	$V_{DD} = 40 \text{ V}, R_L = 4 \Omega, I_D \cong 10 \text{ A},$	-	16	35		
Turn-off delay time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	53	100		
Fall time	t _f		-	27	60		
Turn-on delay time	t _{d(on)}		-	25	50	ns	
Rise time	t _r	$V_{DD} = 40 \text{ V}, R_L = 4 \Omega, I_D \cong 10 \text{ A},$	-	28	60		
Turn-off delay time	t _{d(off)}	$V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$	-	48	100		
Fall time	t _f		-	27	60		
Drain-Source Body Diode Characteristi	cs						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	303	_	
Pulse diode forward current	I _{SM}	-		-	500	Α	
Body diode voltage	V_{SD}	I _S = 10 A, V _{GS} = 0 V	-	0.72	1.1	V	
Body diode reverse recovery time	t _{rr}		-	106	210	ns	
Body diode reverse recovery charge	Q _{rr}	1 40 A 31/31 400 A / T 67 00	-	190	380	nC	
Reverse recovery fall time	ta	$I_F = 10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	55	-		
Reverse recovery rise time	t _b		-	51	-	ns	

Notes

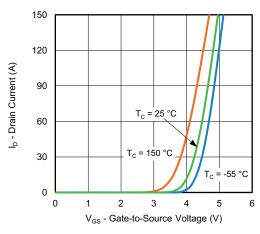
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

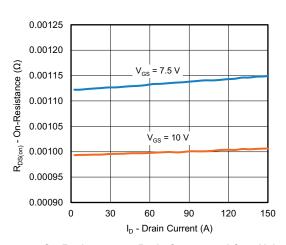




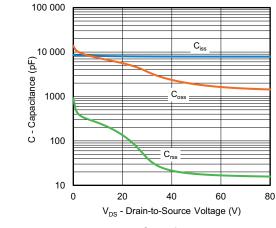
Output Characteristics



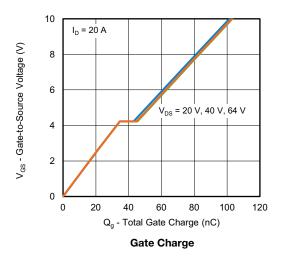
Transfer Characteristics

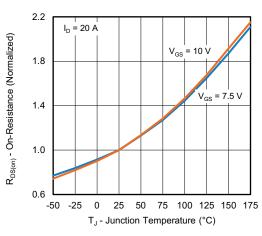


On-Resistance vs. Drain Current and Gate Voltage



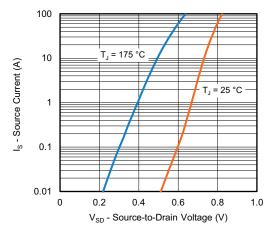
Capacitance



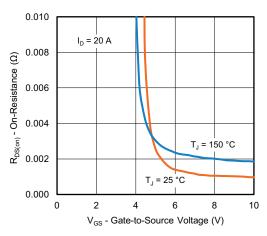


On-Resistance vs. Junction Temperature

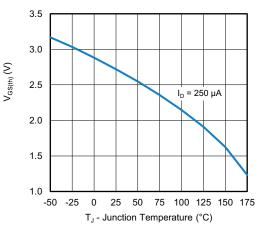




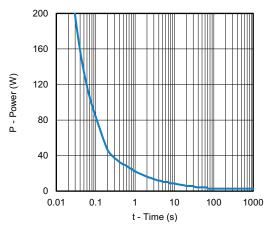
Source-Drain Diode Forward Voltage



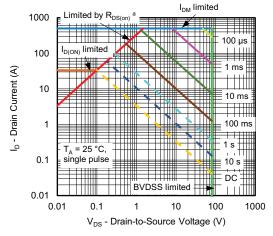
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

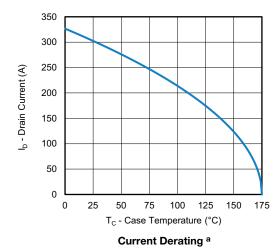


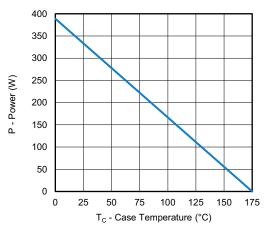
Safe Operating Area, Junction-to-Ambient

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified





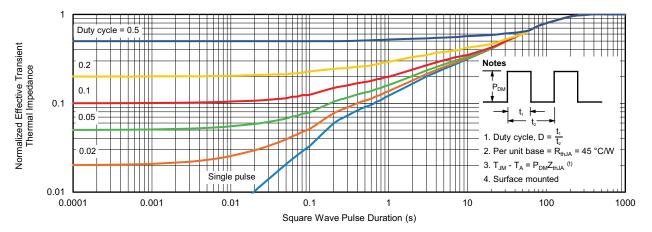


Power, Junction-to-Case

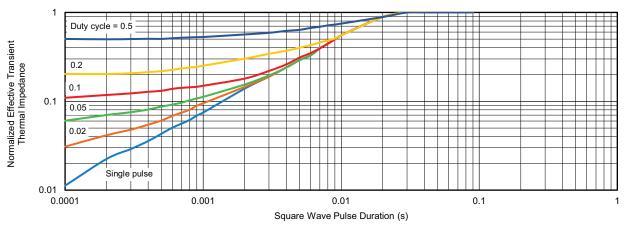
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

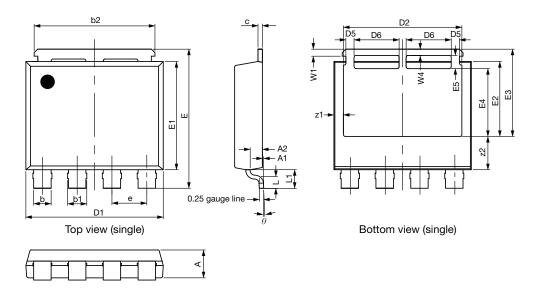


Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® 8 x 8L BWL Case Outline 2



MAX.
0.067
0.005
0.030
0.043
0.046
0.277
0.012
0.315
0.272
0.022
0.106
0.080
0.319
0.249
0.174
0.202
0.157
0.033
0.030
0.045
0.020
0.017
0.026
0.079
5°

ECN: S19-0643-Rev. B, 05-Aug-2019

DWG: 6073

Note

Millimeter will govern



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